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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Application Number	10/695,724
Filing Date	October 28, 2003
First Named Inventor	Eric Frayssinet
Art Unit	2823
Examiner Name	Rori Burch
Attorney Docket Number	15675P314CX

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.'	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume issue number(s), publisher, city and/or country where published.	T²
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	U.S. PAYENY DOCUMENTS								
Examiner		Document Number	Publication Date	Name of Patentee or	Pages, Columns, Lines, Where				
Initials*	Cite No.'	Number - Kind Code ² (if known)	or Issue Date MM-DD-YYYY	Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear				
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Examiner	Cite	Foreign Patent Document			Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	70
Initials*	No.1	Country Code ³ - Number ⁴ - Kind Code ⁶ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document		۲
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